

AVX Multilayer Ceramic Chip Capacitor

Ceramic Chip Capacitors

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Basic Construction – A multilayer ceramic (MLC) capacitor is a monolithic block of ceramic containing two sets of offset, interleaved planar electrodes that extend to two opposite surfaces of the ceramic dielectric. This simple

structure requires a considerable amount of sophistication, both in material and manufacture, to produce it in the quality and quantities needed in today's electronic equipment.

Formulations – Multilayer ceramic capacitors are available in both Class 1 and Class 2 formulations. Temperature compensating formulation are Class 1 and temperature stable and general application formulations are classified as Class 2.

Class 1 – Class 1 capacitors or temperature compensating capacitors are usually made from mixtures of titanates where barium titanate is normally not a major part of the mix. They have predictable temperature coefficients and in general, do not have an aging characteristic. Thus they are the most stable capacitor available. Normally the T.C.s of multilayer ceramic capacitors are NP0 Class 1 temperature compensating capacitors (negative-positive 0 ppm/°C).

Class 2 – Class 2 capacitors are "ferro electric" and vary in capacitance value under the influence of the environmental and electrical operating conditions. Class 2 capacitors are affected by temperature, voltage (both AC and DC), frequency and time. Temperature effects for Class 2 ceramic capacitors are exhibited as non-linear capacitance changes with temperature. The most common temperature stable formulation for MLCs is X7R while Z5U and Y5V are the most common general application formulations.

For additional information on performance changes with operating conditions consult AVX's software, SpiCap.

Effects of Voltage – Variations in voltage have little affect on Class 1 dielectric but does effect the capacitance and dissipation factor of Class 2 dielectrics. The application of DC voltage reduces both the capacitance and dissipation factor while the application of an AC voltage within a reasonable range tends to increase both capacitance and dissipation factor readings. If a high enough AC voltage is applied, eventually it will reduce capacitance just as a DC voltage will. Figure 2 shows the effects of AC voltage.

Figure 2

Capacitor specifications specify the AC voltage at which to measure (normally 0.5 or 1 VAC) and application of the wrong voltage can cause spurious readings. Figure 3 gives the voltage coefficient of dissipation factor for various AC voltages at 1 kilohertz. Applications of different frequencies will affect the percentage changes versus voltages.

D.F. vs. A.C. Measurement Volts

AVX X7R T.C.

Figure 3

The effect of the application of DC voltage is shown in Figure 4. The voltage coefficient is more pronounced for higher K dielectrics. These figures are shown for room temperature conditions. The combination characteristic known as voltage temperature limits which shows the effects of rated voltage over the operating temperature range is shown in Figure 5 for the military BX characteristic.

AVX

Cap. Change vs. D.C. Volts AVX X7R T.C.

Typical Cap. Change vs. Temperature AVX X7R T.C.

Figure 5

Effects of Time – Class 2 ceramic capacitors change capacitance and dissipation factor with time as well as temperature, voltage and frequency. This change with time is known as aging. Aging is caused by a gradual re-alignment of the crystalline structure of the ceramic and produces an exponential loss in capacitance and decrease in dissipation factor versus time. A typical curve of aging rate for semistable ceramics is shown in Figure 6.

If a Class 2 ceramic capacitor that has been sitting on the shelf for a period of time, is heated above its curie point, (125°C for 4 hours or 150°C for $\frac{1}{2}$ hour will suffice) the part will de-age and return to its initial capacitance and dissipation factor readings. Because the capacitance changes rapidly, immediately after de-aging, the basic capacitance measurements are normally referred to a time period sometime after the de-aging process. Various manufacturers use different time bases but the most popular one is one day or twenty-four hours after "last heat." Change in the aging curve can be caused by the application of voltage and other stresses. The possible changes in capacitance due to deaging by heating the unit explain why capacitance changes are allowed after test, such as temperature cycling, moisture resistance, etc., in MIL specs. The application of high voltages such as dielectric withstanding voltages also tends

to de-age capacitors and is why re-reading of capacitance after 12 or 24 hours is allowed in military specifications after dielectric strength tests have been performed.

Effects of Frequency – Frequency affects capacitance and impedance characteristics of capacitors. This effect is much more pronounced in high dielectric constant ceramic formulation that is low K formulations. AVX's SpiCap software generates impedance, ESR, series inductance, series resonant frequency and capacitance all as functions of frequency, temperature and DC bias for standard chip sizes and styles. It is available free from AVX.

AVAK

Effects of Mechanical Stress – High "K" dielectric ceramic capacitors exhibit some low level piezoelectric reactions under mechanical stress. As a general statement, the piezoelectric output is higher, the higher the dielectric constant of the ceramic. It is desirable to investigate this effect before using high "K" dielectrics as coupling capacitors in extremely low level applications.

Reliability – Historically ceramic capacitors have been one of the most reliable types of capacitors in use today. The approximate formula for the reliability of a ceramic capacitor is:

$$
\frac{L_o}{L_t} = \left(\frac{V_t}{V_o}\right)^X \left(\frac{T_t}{T_o}\right)^Y
$$

where

 L_0 = operating life **T**_{**t**} = test temperature and L_t = test life **T_o** = operating temperature
 V_{**r**} = test voltage in °C V_t = test voltage in °C
 V_o = operating voltage $X.Y$ = see text V_o = operating voltage

Historically for ceramic capacitors exponent X has been considered as 3. The exponent Y for temperature effects typically tends to run about 8.

A capacitor is a component which is capable of storing electrical energy. It consists of two conductive plates (electrodes) separated by insulating material which is called the dielectric. A typical formula for determining capacitance is:

$$
C = \frac{.224 \text{ KA}}{t}
$$

- **C** = capacitance (picofarads)
- $K =$ dielectric constant (Vacuum = 1)
- $A =$ area in square inches
- **t** = separation between the plates in inches (thickness of dielectric)
- **.224** = conversion constant

(.0884 for metric system in cm)

Capacitance – The standard unit of capacitance is the farad. A capacitor has a capacitance of 1 farad when 1 coulomb charges it to 1 volt. One farad is a very large unit and most capacitors have values in the micro (10^{-6}) , nano $(10⁻⁹)$ or pico $(10⁻¹²)$ farad level.

Dielectric Constant – In the formula for capacitance given above the dielectric constant of a vacuum is arbitrarily chosen as the number 1. Dielectric constants of other materials are then compared to the dielectric constant of a vacuum.

Dielectric Thickness - Capacitance is indirectly proportional to the separation between electrodes. Lower voltage requirements mean thinner dielectrics and greater capacitance per volume.

Area – Capacitance is directly proportional to the area of the electrodes. Since the other variables in the equation are usually set by the performance desired, area is the easiest parameter to modify to obtain a specific capacitance within a material group.

Energy Stored – The energy which can be stored in a capacitor is given by the formula:

$E = \frac{1}{2}CV^2$

E = energy in joules (watts-sec)

 = applied voltage

C = capacitance in farads

Potential Change – A capacitor is a reactive component which reacts against a change in potential across it. This is shown by the equation for the linear charge of a capacitor:

$$
I_{\text{ideal}} = c \frac{dV}{dt}
$$

where

$$
\mathbf{I} = \text{Current}
$$

C = Capacitance

dV/dt = Slope of voltage transition across capacitor

Thus an infinite current would be required to instantly change the potential across a capacitor. The amount of current a capacitor can "sink" is determined by the above equation.

Equivalent Circuit – A capacitor, as a practical device, exhibits not only capacitance but also resistance and inductance. A simplified schematic for the equivalent circuit is:

C = Capacitance **L** = Inductance **R^s** = Series Resistance **R^p** = Parallel Resistance $\mathbf{R}_{\mathbf{p}}$ $\mathbf{R}_\mathbf{s}$

Reactance – Since the insulation resistance (R_{0}) is normally very high, the total impedance of a capacitor is:

C

 $Z = \sqrt{R_s^2 + (X_c - X_L)^2}$ where **Z** = Total Impedance **R^s** = Series Resistance X_c = Capacitive Reactance = $2 \pi fC$ X_i = Inductive Reactance = 2 π fL

The variation of a capacitor's impedance with frequency determines its effectiveness in many applications.

Phase Angle – Power Factor and Dissipation Factor are often confused since they are both measures of the loss in a capacitor under AC application and are often almost identical in value. In a "perfect" capacitor the current in the capacitor will lead the voltage by 90°.

In practice the current leads the voltage by some other phase angle due to the series resistance R_{s} . The complement of this angle is called the loss angle and:

> Power Factor (P.F.) = $\cos \phi$ or Sine δ Dissipation Factor (D.F.) = tan δ

for small values of δ the tan and sine are essentially equal which has led to the common interchangeability of the two terms in the industry.

Equivalent Series Resistance – The term E.S.R. or Equivalent Series Resistance combines all losses both series and parallel in a capacitor at a given frequency so that the equivalent circuit is reduced to a simple R-C series connection.

Dissipation Factor – The DF/PF of a capacitor tells what percent of the apparent power input will turn to heat in the capacitor.

$$
Dissipation Factor = \frac{E.S.R.}{X_c} = (2 \pi fC) (E.S.R.)
$$

The watts loss are:

Watts loss =
$$
(2 \pi fCV^2)
$$
 (D.F.)

Very low values of dissipation factor are expressed as their reciprocal for convenience. These are called the "Q" or Quality factor of capacitors.

Parasitic Inductance – The parasitic inductance of capacitors is becoming more and more important in the decoupling of today's high speed digital systems. The relationship between the inductance and the ripple voltage induced on the DC voltage line can be seen from the simple inductance equation:

$$
V = L \frac{di}{dt}
$$

The $\frac{di}{dt}$ seen in current microprocessors can be as high as 0.3 A/ns, and up to 10A/ns. At 0.3 A/ns, 100pH of parasitic inductance can cause a voltage spike of 30mV. While this does not sound very drastic, with the Vcc for microprocessors decreasing at the current rate, this can be a fairly large percentage.

Another important, often overlooked, reason for knowing the parasitic inductance is the calculation of the resonant frequency. This can be important for high frequency, bypass capacitors, as the resonant point will give the most signal attenuation. The resonant frequency is calculated from the simple equation:

$$
f_{res} = \frac{1}{2\pi\sqrt{LC}}
$$

Insulation Resistance – Insulation Resistance is the resistance measured across the terminals of a capacitor and consists principally of the parallel resistance R_P shown in the equivalent circuit. As capacitance values and hence the area of dielectric increases, the I.R. decreases and hence the product (C x IR or RC) is often specified in ohm farads or more commonly megohm-microfarads. Leakage current is determined by dividing the rated voltage by IR (Ohm's Law).

Dielectric Strength – Dielectric Strength is an expression of the ability of a material to withstand an electrical stress. Although dielectric strength is ordinarily expressed in volts, it is actually dependent on the thickness of the dielectric and thus is also more generically a function of volts/mil.

Dielectric Absorption - A capacitor does not discharge instantaneously upon application of a short circuit, but drains gradually after the capacitance proper has been discharged. It is common practice to measure the dielectric absorption by determining the "reappearing voltage" which appears across a capacitor at some point in time after it has been fully discharged under short circuit conditions.

Corona – Corona is the ionization of air or other vapors which causes them to conduct current. It is especially prevalent in high voltage units but can occur with low voltages as well where high voltage gradients occur. The energy discharged degrades the performance of the capacitor and can in time cause catastrophic failures.

BASIC CAPACITOR FORMULAS

I. Capacitance (farads)

English: $C = \frac{.224 \text{ K A}}{.224 \text{ K A}}$ $\mathsf{T}_\texttt{D}$ Metric: $C = \frac{.0884 \text{ K A}}{}$ $T_{\rm n}$

- **II. Energy stored in capacitors (Joules, watt sec)** $E = \frac{1}{2}CV^2$
- **III. Linear charge of a capacitor (Amperes)** $I = C \frac{dV}{dt}$ dt
- **IV. Total Impedance of a capacitor (ohms)**

$$
Z=\sqrt{R^2_S+(X_C-X_L)^2}
$$

V. Capacitive Reactance (ohms)

$$
x_C = \frac{1}{2 \pi fC}
$$

VI. Inductive Reactance (ohms)

 $x_L = 2 \pi fL$

VII. Phase Angles:

Ideal Capacitors: Current leads voltage 90° Ideal Inductors: Current lags voltage 90° Ideal Resistors: Current in phase with voltage

VIII. Dissipation Factor (%)

D.F. = tan
$$
\delta
$$
 (loss angle) = $\frac{E.S.R.}{X_C}$ = (2 π fC) (E.S.R.)

IX. Power Factor (%)

 $P.F. =$ Sine δ (loss angle) = Cos ϕ (phase angle) $P.F. =$ (when less than $10\%) = DF$

X. Quality Factor (dimensionless)

Q = Cotan
$$
\delta
$$
 (loss angle) = $\frac{1}{D.F}$.

METRIC PREFIXES SYMBOLS

XI. Equivalent Series Resistance (ohms) E.S.R. = (D.F.) (Xc) = (D.F.) / (2 π fC)

- **XII. Power Loss (watts)** Power Loss = $(2 \pi fCV^2)$ (D.F.)
- **XIII. KVA (Kilowatts)** KVA = 2π fCV² x 10⁻³

XIV. Temperature Characteristic (ppm/°C)

$$
T.C. = \frac{Ct - C_{25}}{C_{25} (T_t - 25)} \times 10^6
$$

XV. Cap Drift (*)
C.D. =
$$
\frac{C_1 - C_2}{C_1}
$$
 x 100

XVI. Reliability of Ceramic Capacitors

$$
\frac{L_o}{L_t} = \left(\frac{V_t}{V_o}\right) \times \left(\frac{T_t}{T_o}\right) \quad \gamma
$$

XVII. Capacitors in Series (current the same)

Any Number:
$$
\frac{1}{C_T} = \frac{1}{C_1} + \frac{1}{C_2} - \frac{1}{C_N}
$$

Two: $C_T = \frac{C_1 C_2}{C_1 + C_2}$

XVIII. Capacitors in Parallel (voltage the same) $C_T = C_1 + C_2 - \cdots + C_N$

XIX. Aging Rate

 $A.R. = % \Delta C / \frac{1}{2}$ C/decade of time

XX. Decibels

$$
db = 20 log \frac{V_1}{V_2}
$$

How to Order

Part Number Explanation

EXAMPLE: 08055A101JAT2A

 $*$ C&D tolerances for \leq 10 pF values.

** See pages 36-39.

Note: Unmarked product is standard. Marked product is available on special request, please contact AVX.

General Specifications

C0G (NP0) is the most popular formulation of the "temperature-compensating," EIA Class I ceramic materials. Modern NP0 formulations contain neodymium, samarium and other rare earth oxides.

NP0 ceramics offer one of the most stable capacitor dielectrics available. Capacitance change with temperature is 0 ±30ppm/°C which is less than ±0.3% ∆ C from -55°C to +125°C. Capacitance drift or hysteresis for NP0 ceramics is negligible at less than $\pm 0.05\%$ versus up to $\pm 2\%$ for films. Typical capacitance change with life is less than ±0.1% for NP0s, one-fifth that shown by most other dielectrics. NP0 formulations show no aging characteristics.

The NP0 formulation usually has a "Q" in excess of 1000 and shows little capacitance or "Q" changes with frequency. Their dielectric absorption is typically less than 0.6% which is similar to mica and most films.

PART NUMBER (see page 7 for complete information and options)

5

A

Capacitance Code

101

A

Terminations T = Plated Ni and Solder **Packaging** $2 = 7"$ Reel Paper/Unmarked

2

T

PERFORMANCE CHARACTERISTICS

Typical Characteristic Curves **

SUMMARY OF CAPACITANCE RANGES VS. CHIP SIZE

Standard Sizes

**For additional information on performance changes with operating conditions consult AVX's software SpiCap.

PREFERRED SIZES ARE SHADED

***IR and vapor phase soldering only recommended.**

NOTES:

For higher voltage chips, see pages 24 and 25.

Capacitance Range

PREFERRED SIZES ARE SHADED

***IR and vapor phase soldering only recommended.**

NOTES:

For higher voltage chips, see pages 24 and 25.

General Specifications

X7R formulations are called "temperature-stable" ceramics and fall into EIA Class II materials. X7R is the most popular of these intermediate dielectric-constant materials. Its temperature variation of capacitance is within \pm 15% from -55°C to +125°C. This capacitance change is non-linear.

Capacitance for X7R varies under the influence of electrical operating conditions such as voltage and frequency. It also varies with time, approximately 1% ∆ C per decade of time, representing about 5% change in ten years.

X7R dielectric chip usage covers the broad spectrum of industrial applications where known changes in capacitance due to applied voltages are acceptable.

PART NUMBER (see page 7 for complete information and options)

PERFORMANCE CHARACTERISTICS

Typical Characteristic Curves**

* Standard Sizes

**For additional information on performance changes with operating conditions consult AVX's software SpiCap.

Capacitance Range

PREFERRED SIZES ARE SHADED

***IR and vapor phase soldering only recommended.**

NOTES:

For higher voltage chips, see pages 24 and 25.

Capacitance Range

AVX

PREFERRED SIZES ARE SHADED

***IR and vapor phase soldering only recommended.**

NOTES:

For higher voltage chips, see pages 24 and 25.

General Specifications

Z5U formulations are "general-purpose" ceramics which are meant primarily for use in limited temperature applications where small size and cost are important. They provide the highest capacitance possible in a given size for the three most popular ceramic formulations. They show wide variations in capacitance under influence of environmental and electrical operating conditions. Their aging rate is approximately 5% per decade or 25% drop in ten years.

Despite their capacitance instability, Z5U formulations are very popular because of their small size, low ESL, low ESR and excellent frequency response. These features are particularly important for decoupling application where only a minimum capacitance value is required.

PART NUMBER (see page 7 for complete information and options)

PERFORMANCE CHARACTERISTICS

Typical Characteristic Curves**

Capacitance Range

PREFERRED SIZES ARE SHADED

***IR and vapor phase soldering only recommended.**

NOTES: **For low profile chips, see page 23.**

Capacitance Range

PREFERRED SIZES ARE SHADES

***IR and vapor phase soldering only recommended.**

NOTES: **For low profile chips, see page 23.**

Y5V Dielectric

General Specifications

Y5V formulations are for general-purpose use in a limited temperature range. They have a wide temperature characteristic of +22% –82% capacitance change over the operating temperature range of –30°C to +85°C.

Y5V's high dielectric constant allows the manufacture of very high capacitance values (up to 4.7 µF) in small physical sizes.

PART NUMBER (see page 7 for complete information and options)

PERFORMANCE CHARACTERISTICS

Y5V Dielectric

Typical Characteristic Curves**

SUMMARY OF CAPACITANCE RANGES VS. CHIP SIZE

* Standard Sizes

**For additional information on performance changes with operating conditions consult AVX's software SpiCap.

Y5V Dielectric

Capacitance Range

PREFERRED SIZES ARE SHADES

***IR and vapor phase soldering only recommended.**

NOTES: **For low profile product, see page 23.**

Low Profile Chips

Z5U & Y5V Dielectric

PART NUMBER (see page 7 for complete information and options)

CAPACITANCE VALUES FOR VARIOUS THICKNESSES Z5U

Y5V

AVAX

High Voltage Chips

For 500V to 5000V Applications

High value, low leakage and small size are difficult parameters to obtain in capacitors for high voltage systems. AVX special high voltage MLC chips capacitors meet these performance characteristics and are designed for applications such as snubbers in high frequency power converters, resonators in SMPS, and high voltage coupling/DC blocking. These high voltage chip designs exhibit low ESRs at high frequencies.

Larger physical sizes than normally encountered chips are used to make high voltage chips. These larger sizes require that special precautions be taken in applying these chips in surface mount assemblies. This is due to differences in the coefficient of thermal expansion (CTE) between the substrate materials and chip capacitors.

PART NUMBER (see page 7 for complete information and options)

High Voltage Chips

For 500V to 5000V Applications

NP0 Dielectric

PERFORMANCE CHARACTERISTICS

C0G (NP0) MAXIMUM CAPACITANCE VALUES

X7R Dielectric PERFORMANCE CHARACTERISTICS

X7R MAXIMUM CAPACITANCE VALUES

General Specifications

Mechanical

END TERMINATION ADHERENCE

Specification

No evidence of peeling of end terminal

Measuring Conditions

After soldering devices to circuit board apply 5N (0.51kg f) for 10 ± 1 seconds, please refer to Figure 1.

Figure 1. Terminal Adhesion

RESISTANCE TO VIBRATION

Specification

Appearance: No visual defects

Capacitance Within specified tolerance

Q, Tan Delta To meet initial requirement

Insulation Resistance

NP0, $X7R \geq$ Initial Value x 0.3 Z5U, Y5V \geq Initial Value x 0.1

Measuring Conditions

Vibration Frequency 10-2000 Hz

Maximum Acceleration 20G

Swing Width 1.5mm

Test Time

X, Y, Z axis for 2 hours each, total 6 hours of test

SOLDERABILITY

Specification

 \geq 95% of each termination end should be covered with fresh solder

Measuring Conditions

Dip device in eutectic solder at 230 \pm 5°C for $2 \pm .5$ seconds

Speed = 1mm/sec

Figure 2. Bend Strength

BEND STRENGTH

Specification

Appearance: No visual defects

Capacitance Variation

NP0: \pm 5% or \pm .5pF, whichever is larger X7R: ≤ ± 12% Z5U: $≤ ± 30%$ $Y5V: ≤ ± 30%$

Insulation Resistance

NP0: ≥ Initial Value x 0.3 $X7R: \geq$ Initial Value x 0.3 $Z5U: \geq$ Initial Value x 0.1 $Y5V:$ > Initial Value x 0.1

Measuring Conditions

Please refer to Figure 2

Deflection: 2mm

Test Time: 30 seconds

RESISTANCE TO SOLDER HEAT

Specification

Appearance:

No serious defects, <25% leaching of either end terminal

Capacitance Variation

NP0: \pm 2.5% or \pm 2.5pF, whichever is greater $X7R: ≤ ± 7.5%$ Z5U: ≤ ± 20% Y5V: ≤ ± 20%

Q, Tan Delta To meet initial requirement

Insulation Resistance To meet initial requirement

Dielectric Strength No problem observed

Measuring Conditions

Dip device in eutectic solder at 260°C, for 1 minute. Store at room temperature for 48 hours (24 hours for NP0) before measuring electrical parameters.

Part sizes larger than 3.20mm x 2.49mm are preheated at 150°C for 30 ±5 seconds before performing test.

General Specifications

THERMAL SHOCK

Specification

Appearance No visual defects

Capacitance Variation

NP0: \pm 2.5% or \pm .25pF, whichever is greater $X7R: \leq \pm 7.5\%$ Z5U: ≤ ± 20% Y5V: ≤ ± 20%

Q, Tan Delta

To meet initial requirement

Insulation Resistance

NP0, X7R: To meet initial requirement Z5U, Y5V: \geq Initial Value x 0.1

Dielectric Strength

No problem observed

Measuring Conditions

Repeat for 5 cycles and measure after 48 hours \pm 4 hours (24 hours for NP0) at room temperature.

IMMERSION

Specification

Appearance

No visual defects

Capacitance Variation

NP0: \pm 2.5% or \pm .25pF, whichever is greater $X7R: \leq \pm 7.5\%$ Z5U: ≤ ± 20% Y5V: ≤ ± 20%

Q, Tan Delta

To meet initial requirement

Insulation Resistance

NP0, X7R: To meet initial requirement Z5U, Y5V: ≥ Initial Value x 0.1

Dielectric Strength

No problem observed

Measuring Conditions

Repeat cycle 2 times and wash with water and dry. Store at room temperature for 48 ± 4 hours (24 hours for NP0) and measure.

MOISTURE RESISTANCE

Specification

Appearance No visual defects

Capacitance Variation

NP0: \pm 5% or \pm .5pF, whichever is greater $X7R: < +10\%$ Z5U: ≤ ± 30% $Y5V: ≤ ± 30%$

Q, Tan Delta

NP0:≥ 30pFQ ≥ 350 ≥ 10pF, < 30pFQ ≥ 275+5C/2 < 10pFQ ≥ 200+10C X7R: Initial requirement + .5% Z5U: Initial requirement + 1% Y5V: Initial requirement + 2%

Insulation Resistance

≥ Initial Value x 0.3

Repeat 20 cycles (1-7) and store for 48 hours (24 hours for NP0) at room temperature before measuring. Steps 7a & 7b are done on any 5 out of first 9 cycles.

General Specifications

Environmental

STEADY STATE HUMIDITY (No Load)

Specification

Appearance

No visual defects

Capacitance Variation

NP0: \pm 5% or \pm .5pF, whichever is greater $X7R: ≤ ± 10%$ Z5U: ≤ ± 30% $Y5V: ≤ ± 30%$

Q, Tan Delta

NP0:≥ 30pFQ ≥ 350 ≥ 10pF, < 30pFQ ≥ 275+5C/2 < 10pFQ ≥ 200+10C X7R: Initial requirement + .5% Z5U: Initial requirement + 1% Y5V: Initial requirement + 2%

Insulation Resistance

≥ Initial Value x 0.3

Measuring Conditions

Store at $85 \pm 5\%$ relative humidity and 85° C for 1000 hours, without voltage. Remove from test chamber and stabilize at room temperature and humidity for 48 $±$ 4 hours (24 $±$ 2 hours for NP0) before measuring.

Charge and discharge currents must be less than 50ma.

LOAD HUMIDITY

Specification

Appearance

No visual defects

Capacitance Variation

NP0: \pm 5% or \pm .5pF, whichever is greater $X7R: ≤ ± 10%$ $Z5U$: ≤ ± 30% $Y5V: ≤ ± 30%$

Q, Tan Delta

NP0: ≥ 30pFQ ≥ 350 ≥ 10pF, < 30pFQ ≥ 275+5C/2 < 10pFQ ≥ 200+10C X7R: Initial requirement + .5% Z5U: Initial requirement + 1% Y5V: Initial requirement + 2%

Insulation Resistance

NP0, X7R: To meet initial value x 0.3 Z5U, Y5V: ≥ Initial Value x 0.1

Charge devices with rated voltage in test chamber set at $85 \pm 5\%$ relative humidity and 85° C for 1000 (+48,-0) hours. Remove from test chamber and stabilize at room temperature and humidity for 48 ± 4 hours (24 \pm 2 hours for NP0) before measuring.

Charge and discharge currents must be less than 50ma.

LOAD LIFE

Specification

Appearance No visual defects

Capacitance Variation

NP0: \pm 3% or \pm .3pF, whichever is greater $X7R: ≤ ± 10%$ Z5U: ≤ ± 30% Y5V: ≤ ± 30%

Q, Tan Delta

NP0: ≥ 30pFQ ≥ 350 ≥ 10pF, < 30pFQ ≥ 275+5C/2 < 10pFQ ≥ 200+10C X7R: Initial requirement + .5% Z5U: Initial requirement + 1% Y5V: Initial requirement + 2%

Insulation Resistance

NP0, X7R: To meet initial value x 0.3 Z5U, Y5V: \geq Initial Value x 0.1

Charge devices with twice rated voltage in test chamber set at $+125^{\circ}C \pm 2^{\circ}C$ for NP0 and X7R, $+85^{\circ} \pm 2^{\circ}$ C for Z5U, and Y5V for 1000 (+48,-0) hours. Remove from test chamber and stabilize at room temperature for 48 ± 4 hours (24 ± 2 hours for NP0) before measuring.

Charge and discharge currents must be less than 50ma.

Part Number Example

MIL Style: CDR01, CDR02, CDR03, CDR04, CDR05, CDR06

Voltage Temperature Limits:

 $BP = 0 \pm 30$ ppm/°C without voltage; 0 ± 30 ppm/°C with rated voltage from -55°C to +125°C $BX = ± 15%$ without voltage; $+15 - 25%$ with rated voltage from -55°C to +125°C

Capacitance:

Two digit figures followed by multiplier (number of zeros to be added) e.g., $101 = 100$ pF

Rated Voltage: $A = 50V$, $B = 100V$

Capacitance Tolerance:

J ±5%, K ±10%, M ±20%

Military Designation Per MIL-C-55681

Termination Finish:

-
-
- $U =$ Base Metallization/Barrier

Lead Alloy)

-
- N = Silver Nickel Gold Metal/Solder Coated*
S = Solder-coated W = Base Metallization/Ba $W =$ Base Metallization/Barrier Metal/Tinned (Tin or Tin/

Failure Rate Level: $M = 1.0\%$, $P = .1\%$, $R = .01\%$, $S = .001\%$

Packaging: Bulk is standard packaging. Tape and reel per RS481 is available upon request.

*Solder shall have a melting point of 200°C or less.

CROSS REFERENCE: AVX/MIL-C-55681/CDR01 THRU CDR06*

*For CDR11, 12, 13, and 14 see AVX Microwave Chip Capacitor Catalog

ľ

Military Part Number Identification CDR01 thru CDR06

Add appropriate termination finish

Capacitance Tolerance

ANAK

CDR06BX474A---

CDR06BP682B--- 6800 J,K BP 100
CDR06BP822B--- 8200 J,K BP 100 CDR06BP822B--- 8200 J,K BP 100

CDR06BP822B--- 10,000 J,K BP 100

CDR06BX394A--- 390,000 K BX 50

CDR06BX474A--- 470,000 K,M BX 50 CDR06BP103B--- 10,000 J,K BP 100
CDR06BX394A--- 390,000 K BX 50
CDR06BX474A--- 470,000 K,M BX 50

CDR06BX394A--- 390,000 K BX
CDR06BX474A--- 470,000 KM BX

Add appropriate failure rate Add appropriate termination finish

Capacitance Tolerance

Military Part Number Identification CDR31 thru CDR35

MIL Style: CDR31, CDR32, CDR33, CDR34, CDR35

Voltage Temperature Limits:

 $BP = 0 \pm 30$ ppm/°C without voltage; 0 ± 30 ppm/°C with rated voltage from -55°C to +125°C $BX = ± 15%$ without voltage; $+15 - 25%$ with rated voltage from -55°C to +125°C

Capacitance:

Two digit figures followed by multiplier (number of zeros to be added) e.g., $101 = 100$ pF

Rated Voltage: $A = 50V$, $B = 100V$

Capacitance Tolerance:

 $C \pm 0.25$ pF, D ± 0.5 pF, F $\pm 1\%$ J ±5%, K ±10%, M ±20%

Military Designation Per MIL-C-55681

Termination Finish:
M = Palladium Silver

-
- $N =$ Silver Nickel Gold
S = Solder-coated
-
- $U =$ Base Metallization/Barrier
Metal/Solder Coated*
- $W =$ Base Metallization/Barrier Metal/Tinned (Tin or Tin/ Lead Alloy)

*Solder shall have a melting point of 200°C or less.

Failure Rate Level: $M = 1.0\%$, $P = .1\%$, $R = .01\%$, $S = .001%$

Packaging: Bulk is standard packaging. Tape and reel per RS481 is available upon request.

CROSS REFERENCE: AVX/MIL-C-55681/CDR31 THRU CDR35

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Military Part Number Identification CDR31

Add appropriate failure rate

Add appropriate termination finish

Capacitance Tolerance

1/ The complete part number will include additional symbols to indicate capacitance tolerance, termination and failure rate level.

Capacitance Tolerance

Military Part Number Identification CDR32

Add appropriate failure rate

Add appropriate termination finish

Capacitance Tolerance

1/ The complete part number will include additional symbols to indicate capacitance tolerance, termination and failure rate level.

Capacitance Tolerance

Add appropriate failure rate Add appropriate termination finish

Military Part Number Identification CDR33/34/35

Add appropriate termination finish

Capacitance Tolerance

1/ The complete part number will include additional symbols to indicate capacitance tolerance, termination and failure rate level.

- Add appropriate termination finish

Capacitance Tolerance

European Detail Specification CECC 32 101-801/Chips

Standard European Ceramic Chip Capacitors

PART NUMBER (example)

RANGE OF APPROVED COMPONENTS

Packaging of Chip Components

Automatic Insertion Packaging

TAPE & REEL QUANTITIES

All tape and reel specifications are in compliance with RS481.

(1) Dependent on chip thickness. Low profile chips shown on page 23 are 5,000 per reel for 7" reel. 0402 size chips are 10,000 per reel on 7" reels and are not available on 13" reels. For 3640 size chip contact factory for quantity per reel.

REEL DIMENSIONS

Metric dimensions will govern.

English measurements rounded and for reference only.

(1)For tape sizes 16mm and 24mm (used with chip size 3640) consult EIA RS-481 latest revision.

Embossed Carrier Configuration

8 & 12 mm Tape Only

8 & 12 mm Embossed Tape Metric Dimensions Will Govern

CONSTANT DIMENSIONS

VARIABLE DIMENSIONS

NOTES:

1. A_0 , B₀, and K_0 are determined by the max. dimensions to the ends of the terminals extending from the component body and/or the body dimensions of the component. The clearance between the end of the terminals or body of the component to the sides and depth of the cavity $(A_0, B_0,$ and $K_0)$ must be within 0.05 mm (.002) min. and 0.50 mm (.020) max. The clearance allowed must also prevent rotation of the component within the cavity of not more than 20 degrees (see sketches C & D).

2. Tape with components shall pass around radius "R" without damage. The minimum trailer length (Note 2 Fig. 3) may require additional length to provide R min. for 12 mm embossed tape for reels with hub diameters approaching N min. (Table 4).

3. G₁ dimension is the flat area from the edge of the sprocket hole to either the outward deformation of the carrier tape between the embossed cavities or to the edge of the cavity whichever is less.

4. G_o dimension is the flat area from the edge of the carrier tape opposite the sprocket holes to either the outward deformation of the carrier tape between the embossed cavity or to the edge of the cavity whichever is less.

- 5. The embossment hole location shall be measured from the sprocket hole controlling the location of the emboss-
- ment. Dimensions of embossment location and hole location shall be applied independent of each other.

6. B₁ dimension is a reference dimension for tape feeder clearance only.

Maximum Component Rotation

Side or Front Sectional View
Sketch "C"

20° maximum component rotation Typical component cavity center line **Typical component** center line Top View
Sketch "D"

в.

Punched Carrier Configuration

8 & 12 mm Tape Only

8 & 12 mm Punched Tape Metric Dimensions Will Govern

User Direction of Feed

CONSTANT DIMENSIONS

VARIABLE DIMENSIONS

NOTES:

1. A₀, B₀, and T are determined by the max. dimensions to the ends of the terminals extending from the component body and/or the body dimensions of the component. The clearance between the ends of the terminals or body of the component to the sides and depth of the cavity (A_0, B_0, A_0) must be within 0.05 mm (.002) min. and 0.50 mm (.020) max. The clearance allowed must also prevent rotation of the component within the cavity of not more than 20 degrees (see sketches A & B).

ANAK

2. Tape with components shall pass around radius "R" without damage.

3. 1.1 mm (.043) Base Tape and 1.6 mm (.063) Max. for Non-Paper Base Compositions.

Side or Front Sectional View

Sketch "A"

Top View
Sketch "B"

Bar Code Labeling Standard

AVX bar code labeling is available and follows latest version of EIA-556-A.

Bulk Case Packaging

- Easier handling
- Smaller packaging volume (1/20 of T/R packaging)
- Easier inventory control
- Flexibility
- Recyclable

CASE DIMENSIONS

BENEFITS BULK FEEDER

CASE QUANTITIES

Appendix 1: MLC Capacitors

PHYSICAL PROPERTIES

The properties of MLC's are decided by their chemical composition and physical makeup. As manufacturers use slightly different compositions and designs this means that all MLC's do not have identical properties. Most systems are, however, based on doped barium titanate raw materials and basically similar designs. There will be minor differences in value for some of the physical constants quoted but these should not prove significant for practical purposes.

Temperature

Coefficient of expansion (CTE)

This varies according to which axis of the chip is being measured.

It should be remembered that in attempting to match circuit board material with MLC's that the dynamic system should be considered (power on temperature rise) not the static system (uniform temperature rise).

Thermal Conductivity

Ceramic 5W/m Kelvin Termination (Ni Bar) 380W/m Kelvin Electrode (Pd/Ag) 140W/m Kelvin

These figures show the problem of predicting the thermal behavior of MLC's each one being different according to its form and number of electrodes.

Appendix 1: MLC Capacitors

Strength

Flexure 140 MPa Fracture toughness 3Gpa

This merely confirms the well known high strength in compression, low strength in tension that ceramics normally have.

Chemical Resistance

Ceramics themselves are very resistant to chemical attack, providing they are processed in a manner which prevents the incidence of cracks or chips in the body. In cases where cracks etc. are present, moisture can penetrate and cause insulation resistance to reduce.

Termination, whether silver/palladium or nickel barrier solder coated, can suffer chemical attack from pollutants in the air or packing materials. In order to preserve their solderability they should be kept in the packing the manufacturer supplied until required for use. Points to watch are the use of paper and rubber bands, which contain sulphur compounds.

Handling

Ceramic chips can easily be damaged and contaminated by poor handling or storage. A chip or crack, contamination by hands or poor storage, use of metal tweezers (the surface or bare ceramic chips is very abrasive) can all induce subsequent defect as described above. Care must be taken to achieve the best results.

TERMINATION TYPES & APPLICATIONS

The capacitor termination must be designed so that it has (a) a good electrical connection to the internal electrode system and (b) has good solderability and leaching properties with normally used fluxes, solders and soldering processes.

Surface mount assembly has permitted the use of a wider range of soldering processes than was traditionally viable for pin-through hole manufacture.

This has, in turn, placed greater demands on the capacitor terminations, especially with regard to wave-soldering and some of the more prolonged reflow techniques.

Storage

Good solderability is maintained for at least twelve months, provided the components are stored in their "as received" packaging at less than 40°C and 70% relative humidity.

Solderability

Terminations to be well tinned after immersion in a 60/40 tin/lead solder bath at 230 \pm 10°C for 5 \pm 1 seconds.

Appendix 1: MLC Capacitors

Component Pad Design

Component pads should be designed to achieve good solder filets and minimize component movement during reflow soldering. Pad designs are given below for the most common sizes of multilayer ceramic capacitors for both wave and reflow soldering. The basis of these designs is:

- Pad width equal to component width. It is permissible to decrease this to as low as 85% of component width but it is not advisable to go below this.
- Pad overlap 0.5mm beneath component.
- Pad extension 0.5mm beyond components for reflow and 1.0mm for wave soldering.

REFLOW SOLDERING

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Appendix 1: MLC Capacitors

WAVE SOLDERING

Dimensions in millimeters (inches)

Component Spacing

For wave soldering components, must be spaced sufficiently far apart to avoid bridging or shadowing (inability of solder to penetrate properly into small spaces). This is less important for reflow soldering but sufficient space must be allowed to enable rework should it be required.

Preheat & Soldering

The rate of preheat should not exceed 4° C/second to prevent thermal shock. A better maximum figure is about 2° C/second.

For capacitors size 1206 and below, with a maximum thickness of 1.25mm, it is generally permissible to allow a temperature differential from preheat to soldering of 150°C. In all other cases this differential should not exceed 100°C.

For further specific application or process advice please consult AVX.

Cleaning

Care should be taken to ensure that the capacitors are thoroughly cleaned of flux residues especially the space beneath the capacitor. Such residues may otherwise become conductive and effectively offer a low resistance bypass to the capacitor.

Ultrasonic cleaning is permissible, the recommended conditions being 8 Watts/litre at 20-45 kHz, with a process cycle of 2 minutes vapor rinse, 2 minutes immersion in the ultrasonic solvent bath and finally 2 minutes vapor rinse.

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Software –

Comprehensive capacitor application software library which includes: SpiCap (for MLC chip capacitors) SpiTan (for tantalum capacitors) SpiCalci (for power supply capacitors) SpiMic (for RF-Microwave capacitors)

For AVX/Elco connector information contact your local AVX/Elco representative

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